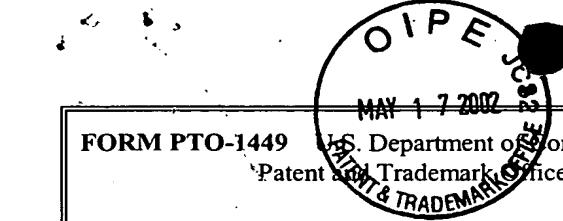


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Filing Date: October 26, 2001

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